Huiyun Liu

List of Publications by Year
in descending order

267 papers	6,267 citations	71102 41 h-index	88630 70 g-index
267 all docs	267 docs citations	267 times ranked	5245 citing authors

#	Article	IF	Citations
1	Design of high-quality reflectors for vertical IIIâ€“V nanowire lasers on Si. Nanotechnology, 2022, 33, 035202.	2.6	3
2	Single-Mode Photonic Crystal Nanobeam Lasers Monolithically Grown on Si for Dense Integration. IEEE Journal of Selected Topics in Quantum Electronics, 2022, 28, 1-6.	2.9	4
3	Multi-wavelength 128 Gbit s^{â^’1} Î» ^{â^’1} PAM4 optical transmission enabled by a 100 GHz quantum dot mode-locked optical frequency comb. Journal Physics D: Applied Physics, 2022, 55, 144001.	2.8	8
4	Thermally-driven formation method for growing (quantum) dots on sidewalls of self-catalysed thin nanowires. Nanoscale Horizons, 2022, 7, 311-318.	8.0	2
5	Recent Progress of Quantum Dot Lasers Monolithically Integrated on Si Platform. Frontiers in Physics, 2022, 10, .	2.1	14
6	The role of different types of dopants in 1.3 Î¼m InAs/GaAs quantum-dot lasers. Journal Physics D: Applied Physics, 2022, 55, 215105.	2.8	6
7	Long-Term Stability and Optoelectronic Performance Enhancement of InAsP Nanowires with an Ultrathin InP Passivation Layer. Nano Letters, 2022, 22, 3433-3439.	9.1	3
8	Multiple radial phosphorus segregations in GaAsP core-shell nanowires. Nano Research, 2021, 14, 157-164.	10.4	3
9	Refractive indices of MBE-grown AlxGa(1â^’<i>x</i>)As ternary alloys in the transparent wavelength region. AIP Advances, 2021, 11, .	1.3	52
10	Multifunctional two-dimensional glassy graphene devices for vis-NIR photodetection and volatile organic compound sensing. Science China Materials, 2021, 64, 1964-1976.	6.3	5
11	Defect-Free Axially Stacked GaAs/GaAsP Nanowire Quantum Dots with Strong Carrier Confinement. Nano Letters, 2021, 21, 5722-5729.	9.1	14
12	Robust Protection of IIIâ€“V Nanowires in Water Splitting by a Thin Compact TiO₂ Layer. ACS Applied Materials & Interfaces, 2021, 13, 30950-30958.	8.0	12
13	Co-Package Technology Platform for Low-Power and Low-Cost Data Centers. Applied Sciences (Switzerland), 2021, 11, 6098.	2.5	6
14	Self-Catalyzed AlGaAs Nanowires and AlGaAs/GaAs Nanowire-Quantum Dots on Si Substrates. Journal of Physical Chemistry C, 2021, 125, 14338-14347.	3.1	5
15	Influence of diameter on temperature dynamics of hot carriers in photoexcited GaAsP nanowires. Physical Review B, 2021, 104, .	3.2	0
16	Optimizing GaAs nanowire-based visible-light photodetectors. Applied Physics Letters, 2021, 119, .	3.3	5
17	Modeling of Ultrafast Waveguided Electro-Absorption Modulator at Telecommunication Wavelength (Î» = 1.55 Î¼m) Based on Intersubband Transition in an InGaAs/AlAs/AlAsSb Asymmetric Coupled Double Quantum Well Lattice-Matched to InP. IEEE Journal of Quantum Electronics, 2021, 57, 1-10.	1.9	0
18	Optoelectronic oscillator for 5G wireless networks and beyond. Journal Physics D: Applied Physics, 2021, 54, 423002.	2.8	12

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19	Resonant enhancement of Raman scattering by surface phonon polaritons in GaAs nanowires. Journal Physics D: Applied Physics, 2021, 54, 475111.	2.8	1
20	Polarization properties of Raman scattering by surface phonon polaritons in GaAsP nanowires. Journal Physics D: Applied Physics, 2021, 54, 475109.	2.8	1
21	Microcavity lasers directly grown on silicon. , 2021, , .		0
22	All-MBE grown InAs/GaAs quantum dot lasers with thin Ge buffer layer on Si substrates. Journal Physics D: Applied Physics, 2021, 54, 035103.	2.8	23
23	Monolithic IIIâ€"V quantum dot lasers on silicon. Frontiers of Nanoscience, 2021, 20, 353-388.	0.6	3
24	Various microcavity lasers monolithically grown on planar on-axis Si (001) substrates. , 2021, , .		0
25	The limits to peak modal gain in p-modulation doped indium arsenide quantum dot laser diodes. , 2021, , .		0
26	Origin of Defect Tolerance in InAs/GaAs Quantum Dot Lasers Grown on Silicon. Journal of Lightwave Technology, 2020, 38, 240-248.	4.6	46
27	Ambipolar and Robust WSe 2 Fieldâ€Effect Transistors Utilizing Selfâ€Assembled Edge Oxides. Advanced Materials Interfaces, 2020, 7, 1901628.	3.7	11
28	Checked patterned elemental distribution in AlGaAs nanowire branches via vaporâ€"liquidâ€"solid growth. Nanoscale, 2020, 12, 15711-15720.	5.6	1
29	Inversion Boundary Annihilation in GaAs Monolithically Grown on Onâ€Axis Silicon (001). Advanced Optical Materials, 2020, 8, 2000970.	7.3	22
30	Theoretical Study on the Effects of Dislocations in Monolithic III-V Lasers on Silicon. Journal of Lightwave Technology, 2020, 38, 4801-4807.	4.6	15
31	Heterostructure and Q-factor engineering for low-threshold and persistent nanowire lasing. Light: Science and Applications, 2020, 9, 43.	16.6	26
32	Droplet manipulation and horizontal growth of high-quality self-catalysed GaAsP nanowires. Nano Today, 2020, 34, 100921.	11.9	3
33	Introducing Huiyun Liu, Editor-in-Chief for Journal of Physics D: Applied Physics. Journal Physics D: Applied Physics, 2020, 53, 150201.	2.8	0
34	Continuous-wave quantum dot photonic crystal lasers grown on on-axis Si (001). Nature Communications, 2020, 11, 977.	12.8	61
35	Spatially Bandgap-Graded MoS2(1â^'x)Se2x Homojunctions for Self-Powered Visibleâ€"Near-Infrared Phototransistors. Nano-Micro Letters, 2020, 12, 26.	27.0	22
36	Self-catalyzed GaAs(P) nanowires and their application for solar cells. Journal Physics D: Applied Physics, 2020, 53, 233001.	2.8	6

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37	Impact of ex-situ annealing on strain and composition of MBE grown GeSn. Journal Physics D: Applied Physics, 2020, 53, 485104.	2.8	4
38	Preferred growth direction of IIIâ€"V nanowires on differently oriented Si substrates. Nanotechnology, 2020, 31, 475708.	2.6	8
39	Carrier dynamics and recombination in silicon doped InAs/GaAs quantum dot solar cells with AlAs cap layers. Semiconductor Science and Technology, 2020, 35, 115018.	2.0	3
40	A needle in a needlestack: exploiting functional inhomogeneity for optimized nanowire lasing. , 2020, , .		1
41	Quantum dot mode-locked frequency comb with ultra-stable 25.5â€‰â€‰GHz spacing between 20Â°C and 120Â°C. Photonics Research, 2020, 8, 1937.	7.0	14
42	Heteroepitaxial Growth of III-V Semiconductors on Silicon. Crystals, 2020, 10, 1163.	2.2	56
43	InAs/GaAs Quantum Dot Microlasers Formed on Silicon Using Monolithic and Hybrid Integration Methods. Materials, 2020, 13, 2315.	2.9	14
44	GaAsP nanowires containing intentional and self-forming quantum dots. , 2020, , .		0
45	Photonic crystal lasers grown on CMOS-compatible on-axis Si(001). , 2020, , .		0
46	Impact of dislocations in monolithic III-V lasers on silicon: a theoretical approach. , 2020, , .		1
47	Electrically pumped continuous-wave O-band quantum-dot superluminescent diode on silicon. Optics Letters, 2020, 45, 5468.	3.3	4
48	IIIâ€"V quantum dot lasers epitaxially grown on Si substrates. , 2019, , 17-39.		3
49	Mid-Wave Infrared InAs/GaSb Type-II Superlattice Photodetector With n-B-p Design Grown on GaAs Substrate. IEEE Journal of Quantum Electronics, 2019, 55, 1-5.	1.9	13
50	Demonstration of Si based InAs/GaSb type-II superlattice p-i-n photodetector. Infrared Physics and Technology, 2019, 101, 133-137.	2.9	17
51	Recent progress in epitaxial growth of IIIâ€"V quantum-dot lasers on silicon substrate. Journal of Semiconductors, 2019, 40, 101302.	3.7	29
52	Investigation into the current loss in InAs/GaAs quantum dot solar cells with Si-doped quantum dots. Journal Physics D: Applied Physics, 2019, 52, 505108.	2.8	0
53	Preface to the Special Topic on Compound Semiconductor Materials and Devices on Si. Journal of Semiconductors, 2019, 40, 100101.	3.7	0
54	Enhanced Performance of InAsP Nanowires with Ultra-thin Passivation Layer. , 2019, , .		0

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55	Nanowire Quantum Dot Surface Engineering for High Temperature Single Photon Emission. ACS Nano, 2019, 13, 13492-13500.	14.6	22
56	IIIâ€“V ternary nanowires on Si substrates: growth, characterization and device applications. Journal of Semiconductors, 2019, 40, 101301.	3.7	15
57	Dynamics of Quantum Dot Lasers on Silicon. , 2019, , .		0
58	InAs/GaAs quantum dot solar cells with quantum dots in the base region. IET Optoelectronics, 2019, 13, 215-217.	3.3	9
59	Stabilization of GaAs photoanodes by <i>in situ</i> deposition of nickel-borate surface catalysts as hole trapping sites. Sustainable Energy and Fuels, 2019, 3, 814-822.	4.9	14
60	Toward electrically driven semiconductor nanowire lasers. Nanotechnology, 2019, 30, 192002.	2.6	28
61	Integration of III-V lasers on Si for Si photonics. Progress in Quantum Electronics, 2019, 66, 1-18.	7.0	86
62	Selective area intermixing of IIIâ€“V quantum-dot lasers grown on silicon with two wavelength lasing emissions. Semiconductor Science and Technology, 2019, 34, 085004.	2.0	4
63	Self-Formed Quantum Wires and Dots in GaAsPâ€“GaAsP Coreâ€“Shell Nanowires. Nano Letters, 2019, 19, 4158-4165.	9.1	15
64	Defect Dynamics in Self-Catalyzed IIIâ€“V Semiconductor Nanowires. Nano Letters, 2019, 19, 4574-4580.	9.1	5
65	Highly Strained IIIâ€“Vâ€“V Coaxial Nanowire Quantum Wells with Strong Carrier Confinement. ACS Nano, 2019, 13, 5931-5938.	14.6	19
66	Degradation of IIIâ€“V Quantum Dot Lasers Grown Directly on Silicon Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-6.	2.9	10
67	A metallic hot-carrier photovoltaic device. Semiconductor Science and Technology, 2019, 34, 064001.	2.0	8
68	MoS₂â€“OH Bilayer-Mediated Growth of Inch-Sized Monolayer MoS₂ on Arbitrary Substrates. Journal of the American Chemical Society, 2019, 141, 5392-5401.	13.7	87
69	Heteroepitaxy of GaP on silicon for efficient and cost-effective photoelectrochemical water splitting. Journal of Materials Chemistry A, 2019, 7, 8550-8558.	10.3	19
70	The effect of post-growth rapid thermal annealing on InAs/InGaAs dot-in-a-well structure monolithically grown on Si. Journal of Applied Physics, 2019, 125, 135301.	2.5	5
71	O-band InAs/GaAs quantum-dot microcavity laser on Si (001) hollow substrate by in-situ hybrid epitaxy. AIP Advances, 2019, 9, 015331.	1.3	14
72	Nanowires for High-Efficiency, Low-Cost Solar Photovoltaics. Crystals, 2019, 9, 87.	2.2	59

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73	Enhanced performance of ZnO nanoparticle decorated all-inorganic CsPbBr₃ quantum dot photodetectors. Journal of Materials Chemistry A, 2019, 7, 6134-6142.	10.3	64
74	Thin Ge buffer layer on silicon for integration of III-V on silicon. Journal of Crystal Growth, 2019, 514, 109-113.	1.5	17
75	Effect of InAs quantum dots capped with GaAs on atomic-scale ordering in Ga0.5In0.5P. Journal of Applied Physics, 2019, 125, 053104.	2.5	2
76	Multi-wavelength DFB laser array in InAs/GaAs quantum dot material epitaxially grown on Silicon. , 2019, , .		0
77	Growth and Fabrication of Highâ€Quality Single Nanowire Devices with Radial pâ€iâ€n Junctions. Small, 2019, 15, 1803684.	10.0	16
78	O-band InAs/GaAs quantum dot laser monolithically integrated on exact (0â€¯0â€¯1) Si substrate. Journal of Crystal Growth, 2019, 511, 56-60.	1.5	31
79	Growth mechanisms for InAs/GaAs QDs with and without Bi surfactants. Materials Research Express, 2019, 6, 015046.	1.6	5
80	Understanding the Bandwidth Limitations in Monolithic 1.3 <i>Î¼</i>m InAs/GaAs Quantum Dot Lasers on Silicon. Journal of Lightwave Technology, 2019, 37, 949-955.	4.6	14
81	Optically-pumped InAs/GaAs quantum-dot microdisk lasers monolithically grown on on-axis Si (001) substrate. , 2019, , .		1
82	Gallium Phosphide photoanode coated with TiO₂ and CoO_x for stable photoelectrochemical water oxidation. Optics Express, 2019, 27, A364.	3.4	18
83	High performance waveguide uni-travelling carrier photodiode grown by solid source molecular beam epitaxy. Optics Express, 2019, 27, 37065.	3.4	12
84	Roadmap of 1300-nm InAs/GaAs quantum dot laser grown on silicon for silicon photonics. , 2019, , .		7
85	III-V Quantum Dot Lasers Monolithically Grown on Silicon. , 2019, , .		3
86	Ultra-low threshold InAs/GaAs quantum dot microdisk lasers on planar on-axis Si (001) substrates. Optica, 2019, 6, 430.	9.3	37
87	Controlling and modelling the wetting properties of III-V semiconductor surfaces using re-entrant nanostructures. Scientific Reports, 2018, 8, 3544.	3.3	4
88	Boosting photocurrent of GaInP top-cell for current-matched IIIâ€“V monolithic multiple-junction solar cells via plasmonic decahedral-shaped Au nanoparticles. Solar Energy, 2018, 166, 181-186.	6.1	8
89	Stable Defects in Semiconductor Nanowires. Nano Letters, 2018, 18, 3081-3087.	9.1	16
90	Highâ€Responsivity Photodetection by a Selfâ€Catalyzed Phaseâ€Pure pâ€GaAs Nanowire. Small, 2018, 14, e1704429.	10.0	54

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91	An Investigation of the Role of Radiative and Nonradiative Recombination Processes in InAs/GaAs $_{1-x}$ Sb $_{x}$ Quantum Dot Solar Cells. IEEE Journal of Photovoltaics, 2018, 8, 487-492.	2.5	0
92	Light-trapping enhanced thin-film III-V quantum dot solar cells fabricated by epitaxial lift-off. Solar Energy Materials and Solar Cells, 2018, 181, 83-92.	6.2	20
93	High Detectivity and Transparent Fewâ€Layer MoS₂/Glassyâ€Graphene Heterostructure Photodetectors. Advanced Materials, 2018, 30, e1706561.	21.0	111
94	Elevated temperature lasing from injection microdisk lasers on silicon. Laser Physics Letters, 2018, 15, 015802.	1.4	14
95	Direct growth of InAs/GaSb type II superlattice photodiodes on silicon substrates. IET Optoelectronics, 2018, 12, 2-4.	3.3	16
96	Type-II InAs/GaAsSb Quantum Dot Solar Cells With GaAs Interlayer. IEEE Journal of Photovoltaics, 2018, 8, 741-745.	2.5	22
97	Demonstration of InAs/InGaAs/GaAs Quantum Dots-in-a-Well Mid-Wave Infrared Photodetectors Grown on Silicon Substrate. Journal of Lightwave Technology, 2018, 36, 2572-2581.	4.6	36
98	Optical properties of beryllium-doped GaSb epilayers grown on GaAs substrate. Infrared Physics and Technology, 2018, 90, 115-121.	2.9	7
99	Doping of Self-Catalyzed Nanowires under the Influence of Droplets. Nano Letters, 2018, 18, 81-87.	9.1	24
100	Bright prospect of using alcohol-soluble Nb2O5 as anode buffer layer for efficient polymer solar cells based on fullerene and non-fullerene acceptors. Organic Electronics, 2018, 52, 323-328.	2.6	14
101	Mid-wave InAs/GaSb Superlattice PiBN Infrared Photodetector Grown on GaAs Substrate. , 2018, , .		0
102	InAs/GaAs Quantum Dot Lasers Monolithically Integrated on Group IV Platform. , 2018, , .		1
103	Degradation Studies of InAs / GaAs QD Lasers Grown on Si. , 2018, , .		1
104	Dynamic Properties of Monolithic 1.3 Î¼m InAs/GaAs Quantum Dot Lasers on Silicon. , 2018, , .		0
105	Increasing Maximum Gain in InAs Quantum Dot Lasers on GaAs and Si. , 2018, , .		0
106	The influence of direct, delta, and modulation QD Si doping on InAs/GaAs quantum dot solar cells. , 2018, , .		1
107	Small-Signal Modulation and Analysis of Monolithic <tex>$1.3 mu mathrm{m}$</tex> InAs/GaAs Quantum Dot Lasers on Silicon. , 2018, , .		2
108	Optimization of 1.3 <i>Âµ</i>m InAs/GaAs quantum dot lasers epitaxially grown on silicon: taking the optical loss of metamorphic epilayers into account. Laser Physics, 2018, 28, 126206.	1.2	5

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109	IIIâ€"V quantum-dot lasers monolithically grown on silicon. Semiconductor Science and Technology, 2018, 33, 123002.	2.0	35
110	InGaN/GaN Multiple Quantum Well Photoanode Modified with Cobalt Oxide for Water Oxidation. ACS Applied Energy Materials, 2018, 1, 6417-6424.	5.1	23
111	Revealing silicon crystal defects by conductive atomic force microscope. Applied Physics Letters, 2018, 113, .	3.3	13
112	Hybrid IIIâ€"V/IV Nanowires: High-Quality Ge Shell Epitaxy on GaAs Cores. Nano Letters, 2018, 18, 6397-6403.	9.1	6
113	Gain Switching of Monolithic 1.3 Î¼m InAs/GaAs Quantum Dot Lasers on Silicon. Journal of Lightwave Technology, 2018, 36, 3837-3842.	4.6	20
114	Epitaxial Growth of Fewâ€Layer Black Phosphorene Quantum Dots on Si Substrates. Advanced Materials Interfaces, 2018, 5, 1801048.	3.7	20
115	Quantum Dot Quantum Cascade Detector on Si Substrate. , 2018, , .		0
116	GaSb and GaSb/AlSb Superlattice Buffer Layers for High-Quality Photodiodes Grown on Commercial GaAs and Si Substrates. Journal of Electronic Materials, 2018, 47, 5083-5086.	2.2	4
117	Physics-Based Modeling and Experimental Study of Si-Doped InAs/GaAs Quantum Dot Solar Cells. International Journal of Photoenergy, 2018, 2018, 1-10.	2.5	13
118	TiO2 nanofiber photoelectrochemical cells loaded with sub-12Ânm AuNPs: Size dependent performance evaluation. Materials Today Energy, 2018, 9, 254-263.	4.7	23
119	13â€‰â€‰Î¼m InAs/GaAs quantum dot lasers on silicon with GaInP upper cladding layers. Photonics Research, 2018, 6, 321.	7.0	17
120	Midwave Infrared Quantum Dot Quantum Cascade Photodetector Monolithically Grown on Silicon Substrate. Journal of Lightwave Technology, 2018, 36, 4033-4038.	4.6	24
121	Monolithic quantum-dot distributed feedback laser array on silicon. Optica, 2018, 5, 528.	9.3	85
122	Theoretical Analysis of a Microring Resonator Array with High Sensitivity and Large Dynamic Range Based on a Multi-Scale Technique. Sensors, 2018, 18, 1987.	3.8	1
123	Two-colour In_{0.5}Ga_{0.5}As quantum dot infrared photodetectors on silicon. Semiconductor Science and Technology, 2018, 33, 094009.	2.0	21
124	Effect of rapid thermal annealing on threading dislocation density in III-V epilayers monolithically grown on silicon. Journal of Applied Physics, 2018, 123, .	2.5	12
125	Light-Emitting GaAs Nanowires on a Flexible Substrate. Nano Letters, 2018, 18, 4206-4213.	9.1	26
126	Low-noise 13â€‰â€‰Î¼m InAs/GaAs quantum dot laser monolithically grown on silicon. Photonics Research, 2018, 6, 1062.	7.0	35

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127	Silicon-based III-V Quantum Dot Materials and Dsevices. , 2018, , .		0
128	Monolithic Integration of 1.3 Âµm III-V Quantum-Dot Lasers on Si for Si Photonics. , 2018, , .		0
129	O-band InAs Quantum Dot Light Sources Monolithically Grown on Si. , 2018, , .		0
130	Resonant scattering probes for terahertz near-field microscopy. , 2018, , .		0
131	Dark Current Analysis of Mid-Wave Quantum Dots-in-a-Well Photodetectors Monolithically Grown on Silicon Substrate. , 2018, , .		0
132	Integrating Sphere Microscopy for Direct Absorption Measurements of Single Nanostructures. ACS Nano, 2017, 11, 1412-1418.	14.6	30
133	Integrating III-V quantum dot lasers on silicon substrates for silicon photonics. , 2017, , .		0
134	Influence of droplet size on the growth of high-quality self-catalyzed GaAsP nanowires. , 2017, , .		0
135	GaAsP nanowires and nanowire devices grown on silicon substrates. Proceedings of SPIE, 2017, , .	0.8	3
136	2.5-Âµm InGaAs photodiodes grown on GaAs substrates by interfacial misfit array technique. Infrared Physics and Technology, 2017, 81, 320-324.	2.9	11
137	Monolithically Integrated Electrically Pumped Continuous-Wave III-V Quantum Dot Light Sources on Silicon. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-10.	2.9	28
138	Silicon-Based Single Quantum Dot Emission in the Telecoms C-Band. ACS Photonics, 2017, 4, 1740-1746.	6.6	10
139	Ten-Fold Enhancement of InAs Nanowire Photoluminescence Emission with an InP Passivation Layer. Nano Letters, 2017, 17, 3629-3633.	9.1	19
140	Nonradiative Step Facets in Semiconductor Nanowires. Nano Letters, 2017, 17, 2454-2459.	9.1	17
141	Solid solution strengthening in GaSb/GaAs: A mode to reduce the TD density through Be-doping. Applied Physics Letters, 2017, 110, .	3.3	13
142	Influence of Si doping on InAs/GaAs quantum dot solar cells with AlAs cap layers. , 2017, , .		0
143	Influence of built-in charge on photogeneration and recombination processes in InAs/GaAs quantum dot solar cells. Journal Physics D: Applied Physics, 2017, 50, 165101.	2.8	5
144	Correlation between size distribution and luminescence properties of spool-shaped InAs quantum dots. Semiconductor Science and Technology, 2017, 32, 055013.	2.0	5

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145	InGaAs and GaAs quantum dot solar cells grown by droplet epitaxy. Solar Energy Materials and Solar Cells, 2017, 161, 377-381.	6.2	39
146	Site-controlled fabrication of silicon nanotips by indentation-induced selective etching. Applied Surface Science, 2017, 425, 227-232.	6.1	11
147	Impact of the growth temperature on the performance of 1.70-eV Al0.22Ga0.78As solar cells grown by MBE. Journal of Crystal Growth, 2017, 475, 322-327.	1.5	2
148	Growth of Pure Zinc-Blende GaAs(P) Coreâ€"Shell Nanowires with Highly Regular Morphology. Nano Letters, 2017, 17, 4946-4950.	9.1	22
149	Novel Concepts for High-Efficiency Lightweight Space Solar Cells. E3S Web of Conferences, 2017, 16, 03007.	0.5	9
150	Sub-monolayer quantum dot quantum cascade mid-infrared photodetector. Applied Physics Letters, 2017, 111, .	3.3	24
151	Si-Doped InAs/GaAs Quantum Dot Solar Cell with Alas Cap Layers. E3S Web of Conferences, 2017, 16, 16001.	0.5	2
152	III-IV quantum dot lasers epitaxially grown on Si. , 2017, , .		1
153	Resonant scattering probes in the terahertz range. , 2017, , .		0
154	Electrically pumped continuous-wave 13 Âµm InAs/GaAs quantum dot lasers monolithically grown on on-axis Si (001) substrates. Optics Express, 2017, 25, 4632.	3.4	102
155	Resonant terahertz probes for near-field scattering microscopy. Optics Express, 2017, 25, 27874.	3.4	11
156	Monolithic Integration of III-V Quantum Dot Lasers on Silicon for Silicon Photonics. , 2017, , .		0
157	High-performance InAs/GaAs quantum-dot laser didoes monolithically grown on silicon for silicon photonics. , 2017, , .		0
158	Heat-sink free CW operation of injection microdisk lasers grown on Si substrate with emission wavelength beyond 13â€‰â€‰Î¼m. Optics Letters, 2017, 42, 3319.	3.3	40
159	MBE growth of 1.7eV Al0.2Ga0.8As and 1.42eV GaAs solar cells on Si using dislocations filters: an alternative pathway toward III-V/ Si solar cells architectures. , 2017, , .		0
160	Ultra-smooth glassy graphene thin films for flexible transparent circuits. Science Advances, 2016, 2, e1601574.	10.3	59
161	Long lifetime quantum-dot laser monolithically grown on silicon. , 2016, , .		1
162	Bias-free and compact mode-matched excitation of THz coaxial waveguides. , 2016, , .		2

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163	Accurate modelling and measurement of the impedance match between UTC photodiodes and THz antennas. , 2016, , .		0
164	Generation of radially-polarized terahertz pulses for coupling into coaxial waveguides. Scientific Reports, 2016, 6, 38926.	3.3	12
165	Humidity effects on tribochemical removal of GaAs surfaces. Applied Physics Express, 2016, 9, 066703.	2.4	14
166	Deep-etched III-V lasers grown directly on silicon substrates. , 2016, , .		0
167	1.7eV Al0.2Ga0.8As solar cells epitaxially grown on silicon by SSMBE using a superlattice and dislocation filters. , 2016, , .		5
168	Optoelectronic characterization of carrier extraction in a hot carrier photovoltaic cell structure. Journal of Optics (United Kingdom), 2016, 18, 074003.	2.2	13
169	Analysing radiative and non-radiative recombination in InAs QDs on Si for integrated laser applications. Proceedings of SPIE, 2016, , .	0.8	0
170	Optimizations of Defect Filter Layers for 1.3-Î¼m InAs/GaAs Quantum-Dot Lasers Monolithically Grown on Si Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2016, 22, 50-56.	2.9	69
171	Metamorphic IIIâ€“V semiconductor lasers grown on silicon. MRS Bulletin, 2016, 41, 218-223.	3.5	47
172	Monolithically Integrated InAs/GaAs Quantum Dot Mid-Infrared Photodetectors on Silicon Substrates. ACS Photonics, 2016, 3, 749-753.	6.6	63
173	Growth of high-quality self-catalyzed core-shell GaAsP nanowires on Si substrates. Proceedings of SPIE, 2016, , .	0.8	0
174	Al0.2Ga0.8As Solar Cells Monolithically Grown on Si and GaAs by MBE for III-V/Si Tandem Dual-junction Applications. Energy Procedia, 2016, 92, 661-668.	1.8	9
175	Effect of interface oxides on shear properties of hot-rolled stainless steel clad plate. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2016, 669, 344-349.	5.6	73
176	Modelling and measurement of the absolute level of power radiated by antenna integrated THz UTC photodiodes. Optics Express, 2016, 24, 11793.	3.4	21
177	Silicon-based III-V quantum dot devices for silicon photonics. , 2016, , .		0
178	Temperature-Dependent Photoluminescence Characteristics of InAs/GaAs Quantum Dots Directly Grown on Si Substrates. Chinese Physics Letters, 2016, 33, 044207.	3.3	4
179	InAs/GaAs quantum-dot light emitters monolithically grown on Si substrate. , 2016, , .		0
180	Si-Doped InAs/GaAs Quantum-Dot Solar Cell With AlAs Cap Layers. IEEE Journal of Photovoltaics, 2016, 6, 906-911.	2.5	16

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181	Simulation study of GaAsP/Si tandem cells including the impact of threading dislocations on the luminescent coupling between the cells. Proceedings of SPIE, 2016, , .	0.8	0
182	Defect-Free Self-Catalyzed GaAs/GaAsP Nanowire Quantum Dots Grown on Silicon Substrate. Nano Letters, 2016, 16, 504-511.	9.1	42
183	Simulation study of GaAsP/Si tandem solar cells. Solar Energy Materials and Solar Cells, 2016, 145, 206-216.	6.2	26
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